

## PATENT

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Examiner : R. Booth

KATHY LONGENECKER  
(Printed or typed name of person signing the certificate)  
Kathy Longenecker  
(Signature of the person signing the certificate)

Dear Sir:

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT  
BEFORE MAILING DATE OF EITHER A FINAL ACTION  
OR NOTICE OF ALLOWANCE (37 CFR 1.97(c))

### Time of Transmittal of Accompanying Information Disclosure Statement

1. The Information Disclosure Statement transmitted herewith is being filed after the mailing date of the first Office Action on the merits.

The patents, publications and other information herein are listed below and on the attached Form PTO-1449. Copies of the listed references are submitted herewith.

180.00 OP

-100-08

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DOCKET NO. 94-C-096C2  
U.S. SERIAL NO. 09/517,987  
PATENT

<u>U.S. Patent No.</u>	<u>Inventor</u>	<u>Date</u>
4,450,620	Fuls, et al	5/1984
4,663,825	Maeda	5/1987
4,676,867	Elkins et al	6/1987
4,775,644	Szeto	10/1988
4,807,013	Manocha	2/1989
4,841,347	Hsu	6/1989
4,845,047	Holloway, et al.	7/1989
4,859,620	Wei, et al.	8/1989
4,868,138	Chan, et al.	9/1989
4,937,643	Deslauriers, et al.	6/1990
4,977,108	Haskell	12/1990
5,084,419	Sakao	1/1992
5,158,903	Hori, et al.	10/1992
5,182,619	Pfiester	1/1993
5,192,992	Kim, et al.	3/1993
5,241,193	Pfiester, et al.	8/1993
5,319,232	Pfiester	6/1994
5,341,016	Prall, et al.	8/1994
5,346,587	Doan, et al.	9/1994
5,365,081	Yamazaki, et al.	11/1994
5,374,574	Kwon	12/1994
5,376,578	Hsu, et al.	12/1994
5,422,289	Pierce	6/1995
5,434,096	Chu, et al.	7/1995
5,602,056	Jain, et al.	2/1997
5,635,425	Chen	6/1997
5,682,055	Huang, et al.	10/1997
5,683,924	Chan, et al.	11/1997
5,798,278	Chan, et al.	08/1998
5,955,770	Chan, et al.	09/1999
<u>Foreign Patent No.</u>	<u>Country</u>	<u>Date</u>
JP 60 103671	Japan	6/1985
EP 0 334 761 A1	EPO	9/1989
JP 02 009134	Japan	1/1990

Publication

G. Quieirolo et al., "Dpoant Activation, Carrier Mobility, and TEM Studies in Polycrystalline Silicon Films," J. Electrochem. Soc. vol. 37, no. 3, pp. 967-970 (March 1990).

C.S. Pai et al, "Chemical Vapor Deposition of Selective Epitaxial Silicon Layers," J. Electrochem. Soc. vol. 137 no. 3, pp. 971-976 (March 1990).

**Certification or Fee**

2. Accompanying this transmittal is

— a certification as specified in 37 CFR 1.97(e)

OR

X the fee \$180.00 set forth in 37 CFR 1.17(p) for submission of an Information Disclosure Statement under §1.97(c).

**Fee Payment**

3. X Applicant elects the option to pay the fee set forth in 37 CFR 1.17(p) for submission of an Information Disclosure Statement under §1.97(c).

X Attached is a check in the amount of \$180.00.

4. — No fee required - 37 CFR 1.97(e) Certification enclosed.

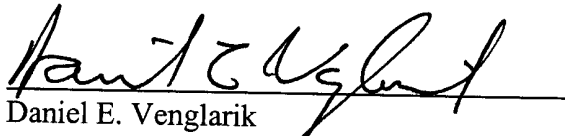
Applicant hereby expressly reserves the right to swear behind the effective dates of any of the above Patents and to question the relevance and materiality of the Patents and Publications listed herein, in whole, in part, or in combination, subsequent to filing this Information Disclosure Statement.

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Respectfully submitted,

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